

IDS 10/24/2000 P.

BEST AVAILABLE COPY

Form PTO-1449 U.S. Department of Commerce (Rev. 8-83) Patent and Trademark Office		Attorney Docket No. 0756-2230	Serial No. 08/818,884
<b>INFORMATION DISCLOSURE STATEMENT</b> (Use several sheets if necessary)		Applicant: Shunpei YAMAZAKI, et al.	
		Filing Date: September 5, 2000	Group: 2871
<b>OTHER DOCUMENTS</b> (Including Author, Title, Date, Page(s), etc.)			
DN		VLSI Technology, Edited by S.M. Sze., McGraw-Hill Book Company, A Chapter 6 Dielectric and Polysilicon F Deposition@, A.C. Adams, pp. 233-235*	
		Scheid, et al., A Super Large Grain Polycrystalline Silicon Obtained From Pyrolysis of Si <sub>2</sub> H <sub>6</sub> and Annealing@, J. appl. Phys., Vol. 29, No. 11, Nov. 1990, pp. L 2105-2107*	
		Blum et al., A Low Pressure CVD Process for Micro and Polycrystalline Silicon@, IBM Technical Disclosure Bulletin, Vol. 26, No. 3A, Aug. 1983, pp. 921-922*	
		Madsen et al., A In Situ Doping of Silicon Films Prepared by Low Pressure Chemical Vapor Deposition Using Disilane and Phosphine@, J. Electrochem. Soc., Vol. 137, No. 7, July 1990, pp. 2246-2251*	
		Wolf et al., A Silicon Processing for the VLSI Era@, Vol. 1: Process Technology, Lattice Press, Sunset Beach, CA (1986), pp. 175-176*	
		H. Ohshima et al., A Future Trends for TFT Integrated Circuits on Glass Substrates@, IEDM (IEEE 1989), pp. 157-160*	
		Journal of Non-Crystalline Solids, Vols. 59, 60, Dec. 1983, Part II, pp. 731-734, Proceedings of the Xth International Conference on Amorphous and Liquid Semiconductors, Tokyo, Japan, Aug 22-26, 1983, C.C. Tsai et al.*	
		Solar Cells 2, (1980), A Investigation of the Hydrogen and Impurity Contents of Amorphous Silicon by Secondary Ion Mass Spectrometry@, Charles MaGee and David E. Carlson, RCA Laboratories, Princeton, NJ pp. 365-376*	
DN	5/5/8	Hydrogenated Amorphous Silicon I Structure, Preparation, and Devices@, Edited by J.D. Joannopoulos and G. Lucovsky, Springer-Verlag, Berlin Heidelberg, New York, Tokyo 1984, pp. 8-9 & 34-41 & 38-41 (DN)	
		Haralis et al., A High-Performance Thin Film Transistors in Low-Temperature Crystallized LPCVD Amorphous Silicon Films@, IEEE Electron Device Letters, Vol. EDL-8, No. 8, Aug. 1987, pp. 161-164*	
		A (Invited) Amorphous Silicon Transistors and Integrated Circuits@, Masakiyo Matsumura, Japanese Journal of Applied Physics, Vol. 22 (1983), Supplement 22-1, pp. 487-491*	
DN	5/5/8	Lewis, et al., "ACTIVE MATRIX LIQUID CRYSTAL DISPLAY DESIGN USING LOW AND HIGH TEMPERATURE PROCESSED POLYSILICON TFTS," CH2865-4/90/0000-0843, IEDM90, pp. 843-846.	
Examiner		Date Considered	
DN WLEN		9/18/04	